

74HC139-Q100; 74HCT139-Q100

Dual 2-to-4 line decoder/demultiplexer

Rev. 1 — 19 June 2014

Product data sheet

1. General description

The 74HC139-Q100; 74HCT139-Q100 decodes two binary weighted address inputs (nA_0 , nA_1) to four mutually exclusive outputs ($n\bar{Y}_0$ to $n\bar{Y}_3$). Each decoder features an enable input ($n\bar{E}$). When $n\bar{E}$ is HIGH all outputs are forced HIGH. The enable input can be used as the data input for a 1-to-4 demultiplexer application. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Input levels:
 - ◆ For 74HC139-Q100: CMOS level
 - ◆ For 74HCT139-Q100: TTL level
- Demultiplexing capability
- 2 independent 2-to-4 decoders
- Multifunction capability
- Suitable for memory decoding, data routing or code conversion
- Complies with JEDEC standard no. 7A
- Active LOW mutually exclusive outputs
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\ \Omega$)
- Multiple package options



3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC139D-Q100 74HCT139D-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC139DB-Q100 74HCT139DB-Q100				
74HC139PW-Q100 74HCT139PW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

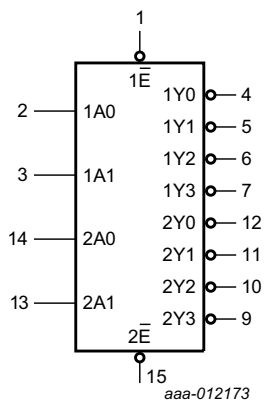


Fig 1. Logic symbol

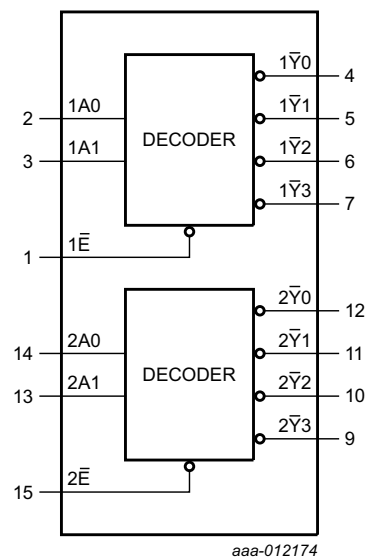
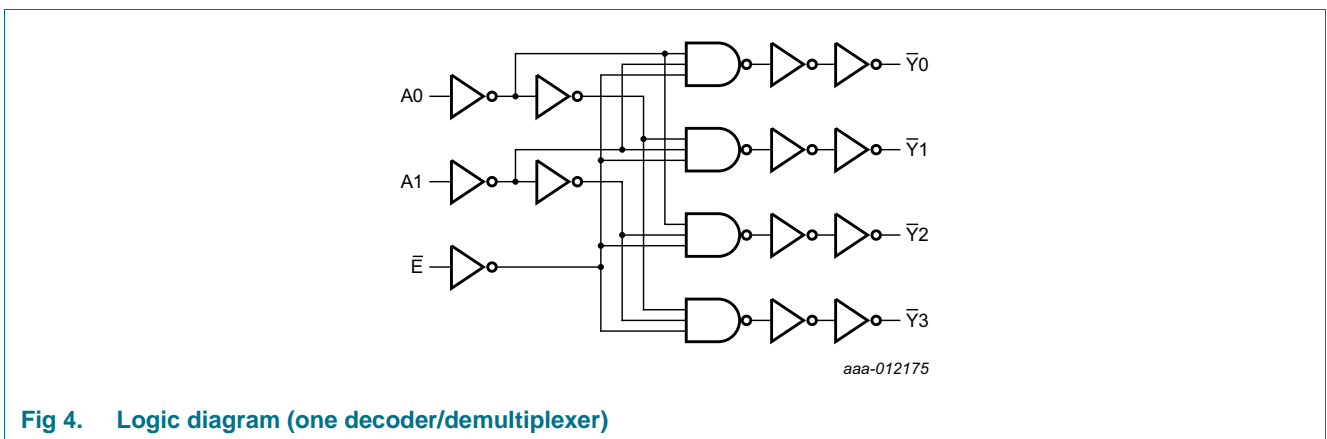
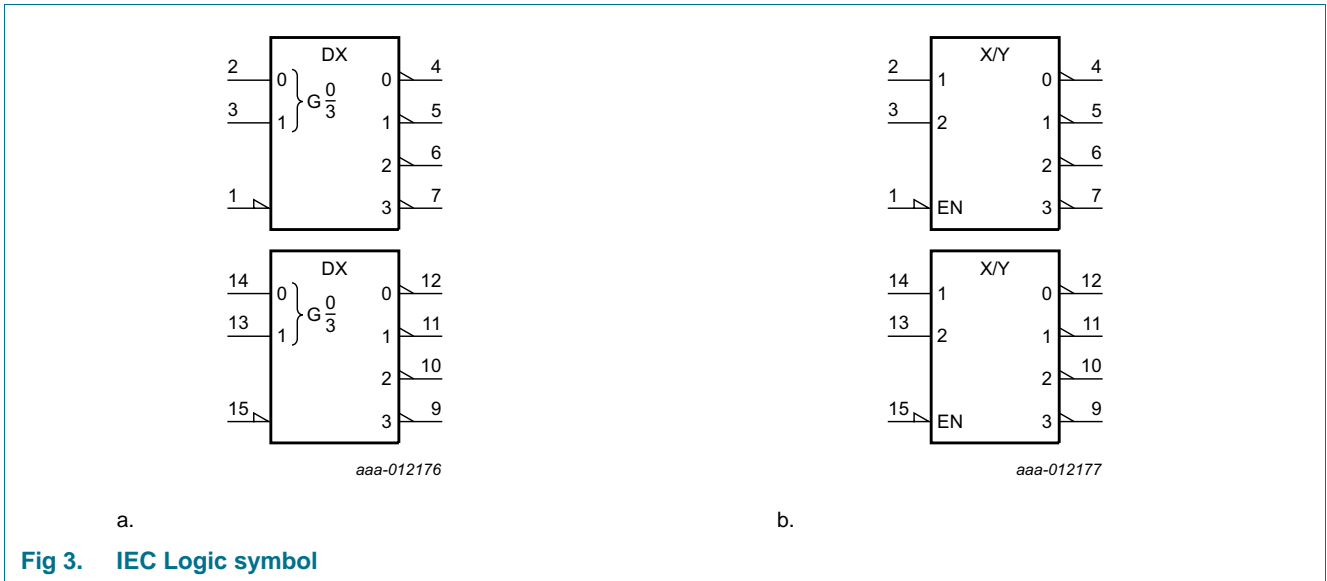


Fig 2. Functional diagram



5. Pinning information

5.1 Pinning

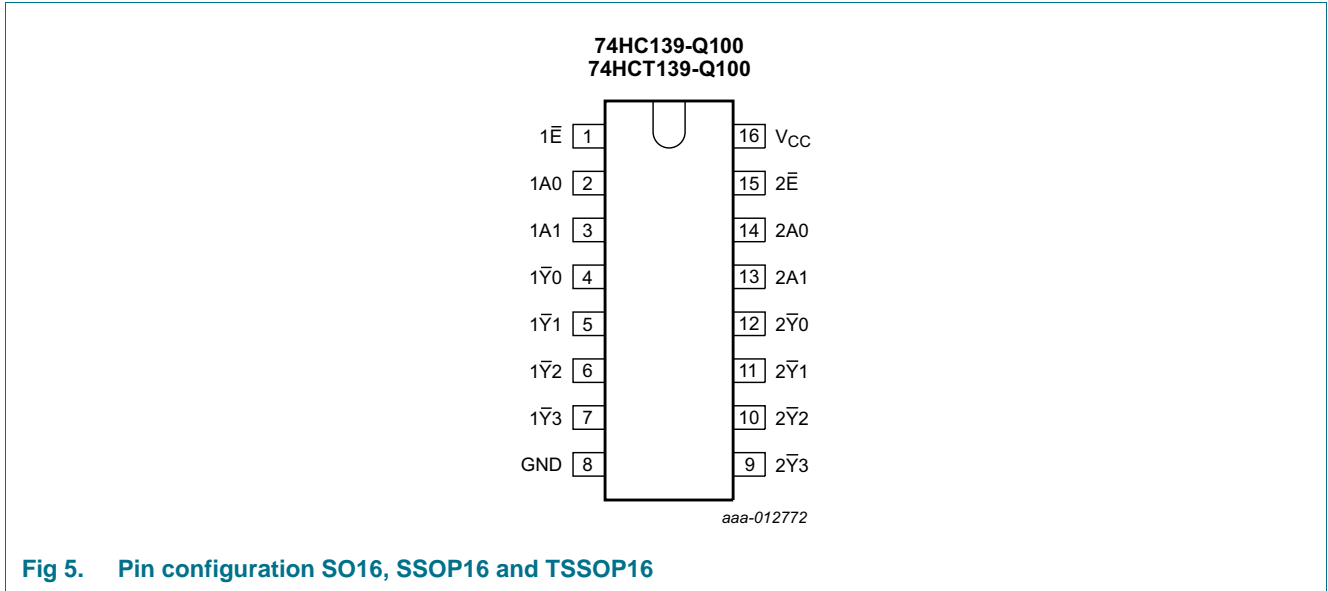


Fig 5. Pin configuration SO16, SSOP16 and TSSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1E-bar, 2E-bar	1, 15	enable input (active LOW)
1A0, 1A1	2, 3	address input
1Y0-bar, 1Y1-bar, 1Y2-bar, 1Y3-bar	4, 5, 6, 7	output (active LOW)
GND	8	ground (0 V)
2Y0-bar, 2Y1-bar, 2Y2-bar, 2Y3-bar	12, 11, 10, 9	output (active LOW)
2A0, 2A1	14, 13	address input
VCC	16	positive supply voltage

6. Functional description

Table 3. Function table^[1]

Control	Input		Output			
	nA1	nA0	nY3	nY2	nY1	nY0
H	X	X	H	H	H	H
L	L	L	H	H	H	L
L	L	H	H	H	L	H
L	H	L	H	L	H	H
L	H	H	L	H	H	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CC}	supply voltage		-0.5	+7	V	
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA	
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA	
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	± 25	mA	
I_{CC}	supply current		-	50	mA	
I_{GND}	ground current		-50	-	mA	
T_{stg}	storage temperature		-65	+150	°C	
P_{tot}	total power dissipation					
	SO16 package		[1]	-	500	mW
	SSOP16 package		[2]	-	500	mW
	TSSOP16 package		[2]	-	500	mW

[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

[2] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC139-Q100			74HCT139-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb}						Unit	
			25 °C			-40 °C to +85 °C		-40 °C to +125 °C		
			Min	Typ	Max	Min	Max	Min		Max
74HC139-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
I _O = -5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V		
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V		
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	-	±5.0	-	±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb}						Unit	
			25 °C			-40 °C to +85 °C		-40 °C to +125 °C		
			Min	Typ	Max	Min	Max	Min		Max
74HCT139-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{oz}	OFF-state output current	per input pin; V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; other inputs at V _{CC} or GND; V _{CC} = 5.5 V; I _O = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		per input pin; 1An inputs	-	70	252	-	315	-	343	μA
		per input pin; 2An inputs	-	70	252	-	315	-	343	μA
		per input pin; n \bar{E} inputs	-	135	486	-	607.5	-	661.5	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	T_{amb}						Unit	
			25 °C			-40 °C to +85 °C		-40 °C to +125 °C		
			Min	Typ	Max	Min	Max	Min		Max
74HC139-Q100										
t_{pd}	propagation delay	nAn to $n\bar{Y}n$; see Figure 6 ^[1]								
		$V_{CC} = 2.0$ V	-	39	145	-	180	-	220	ns
		$V_{CC} = 4.5$ V	-	14	29	-	36	-	44	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	11	-	-	-	-	-	ns
		$V_{CC} = 6.0$ V	-	11	25	-	31	-	38	ns
		$n\bar{E}$ to $n\bar{Y}n$; see Figure 7 ^[1]								
		$V_{CC} = 2.0$ V	-	33	135	-	170	-	205	ns
		$V_{CC} = 4.5$ V	-	12	27	-	34	-	41	ns
t_t	transition time	$n\bar{Y}n$; see Figure 6 and Figure 7 ^[2]								
		$V_{CC} = 2.0$ V	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5$ V	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0$ V	-	6	13	-	16	-	19	ns
C_{PD}	power dissipation capacitance	$C_L = 50$ pF; $f = 1$ MHz; $V_I = GND$ to V_{CC} ^[3]	-	42	-	-	-	-	-	pF
74HCT139-Q100										
t_{pd}	propagation delay	nAn to $n\bar{Y}n$; see Figure 6 ^[1]								
		$V_{CC} = 4.5$ V	-	16	34	-	43	-	51	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	13	-	-	-	-	-	ns
		$n\bar{E}$ to $n\bar{Y}n$; see Figure 7 ^[1]								
		$V_{CC} = 4.5$ V	-	16	34	-	43	-	51	ns
t_t	transition time	$n\bar{Y}n$; see Figure 6 and Figure 7 ^[2]								
		$V_{CC} = 4.5$ V	-	7	15	-	19	-	22	ns

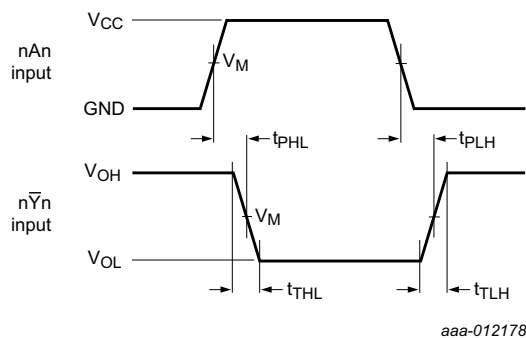
Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	T_{amb}						Unit	
			25 °C			-40 °C to +85 °C		-40 °C to +125 °C		
			Min	Typ	Max	Min	Max	Min		Max
C_{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}$; $f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$ [3]	-	44	-	-	-	-	-	pF

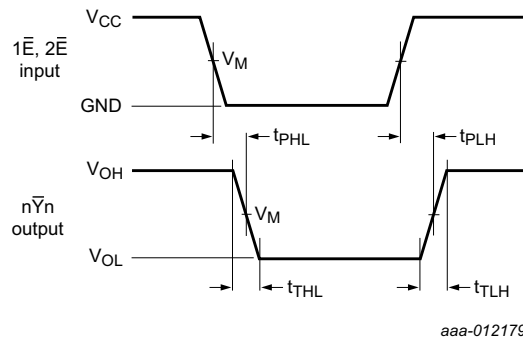
- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delay input (nAn) to output (nYn) and transition time output (nYn)



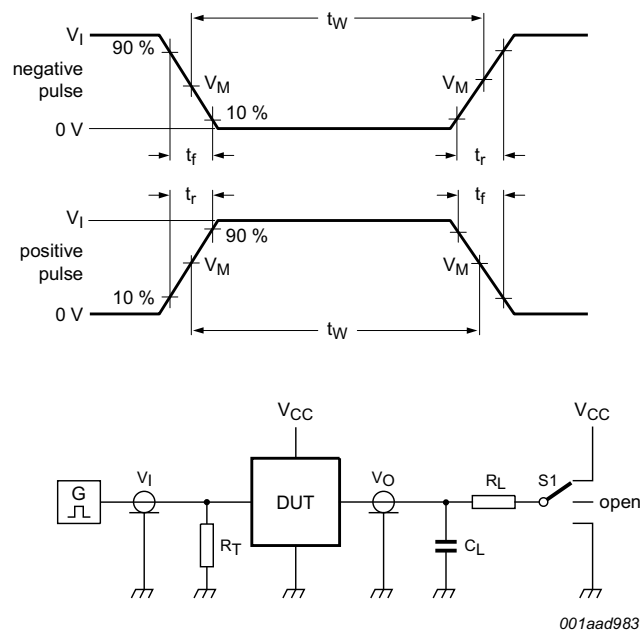
Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Propagation delay enable input (\overline{nE}) to output (\overline{nYn}) and transition time output (\overline{nYn})

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC139-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74HCT139-Q100	1.3 V	1.3 V



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 8. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC139-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT139-Q100	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

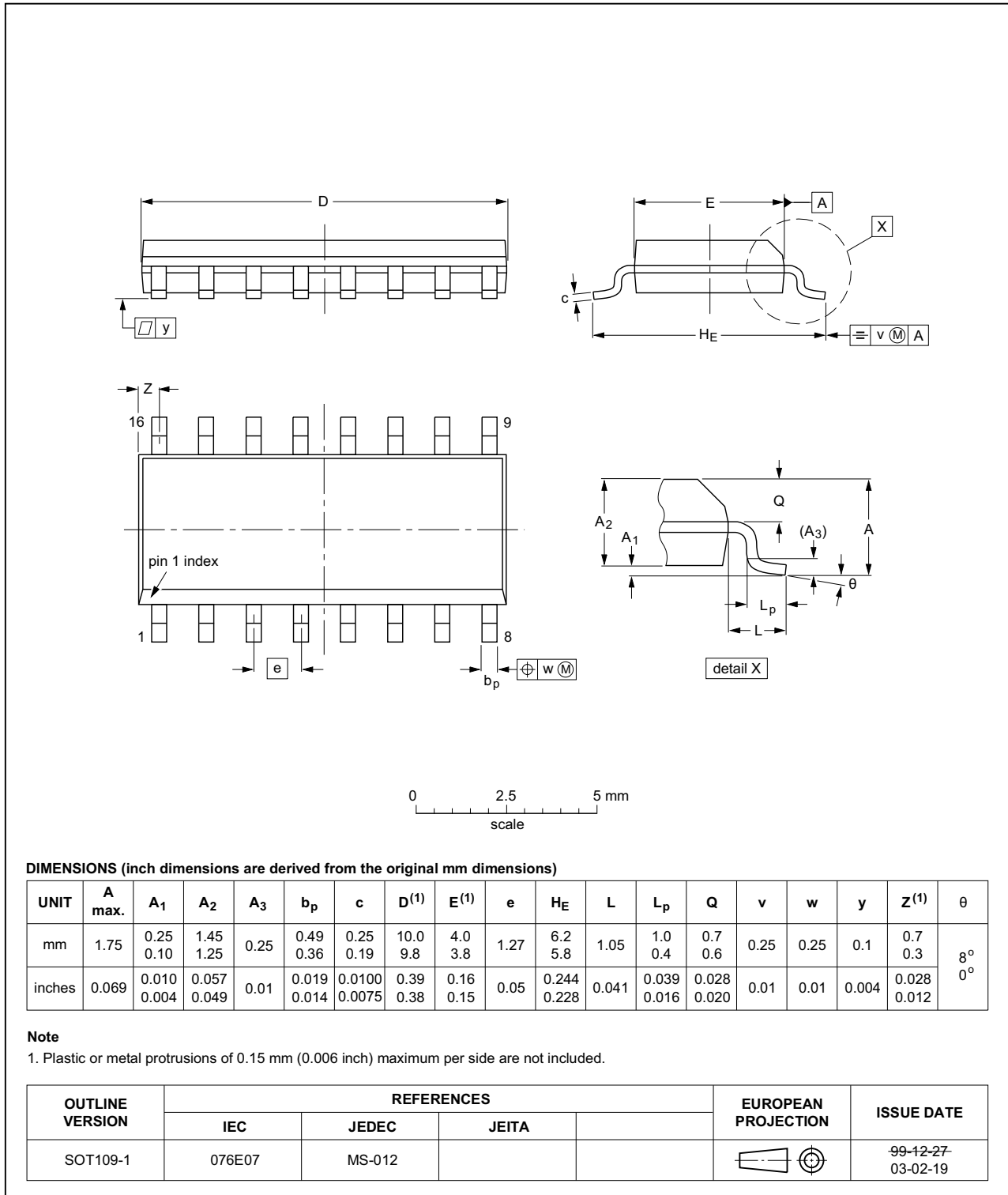


Fig 9. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

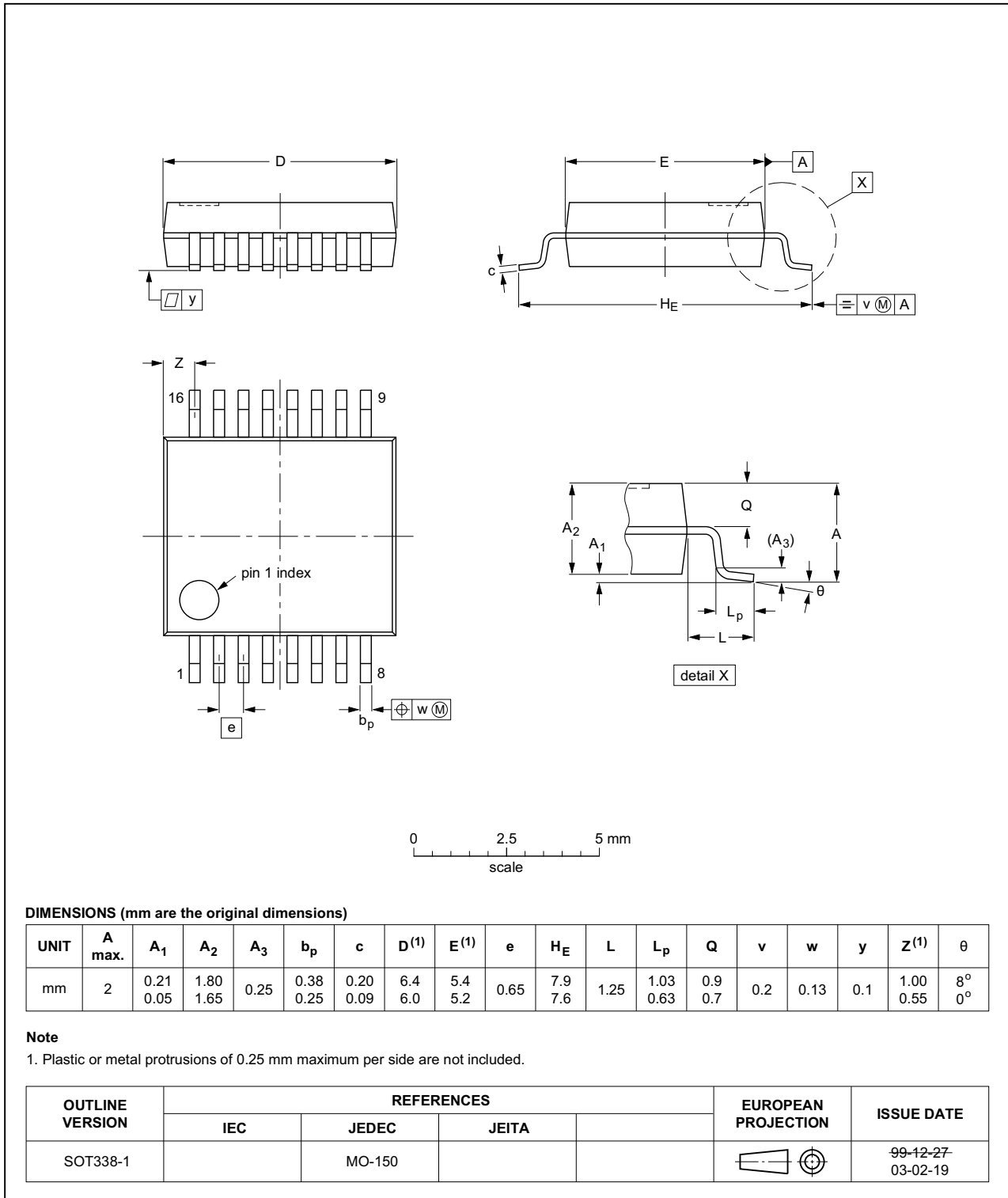


Fig 10. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

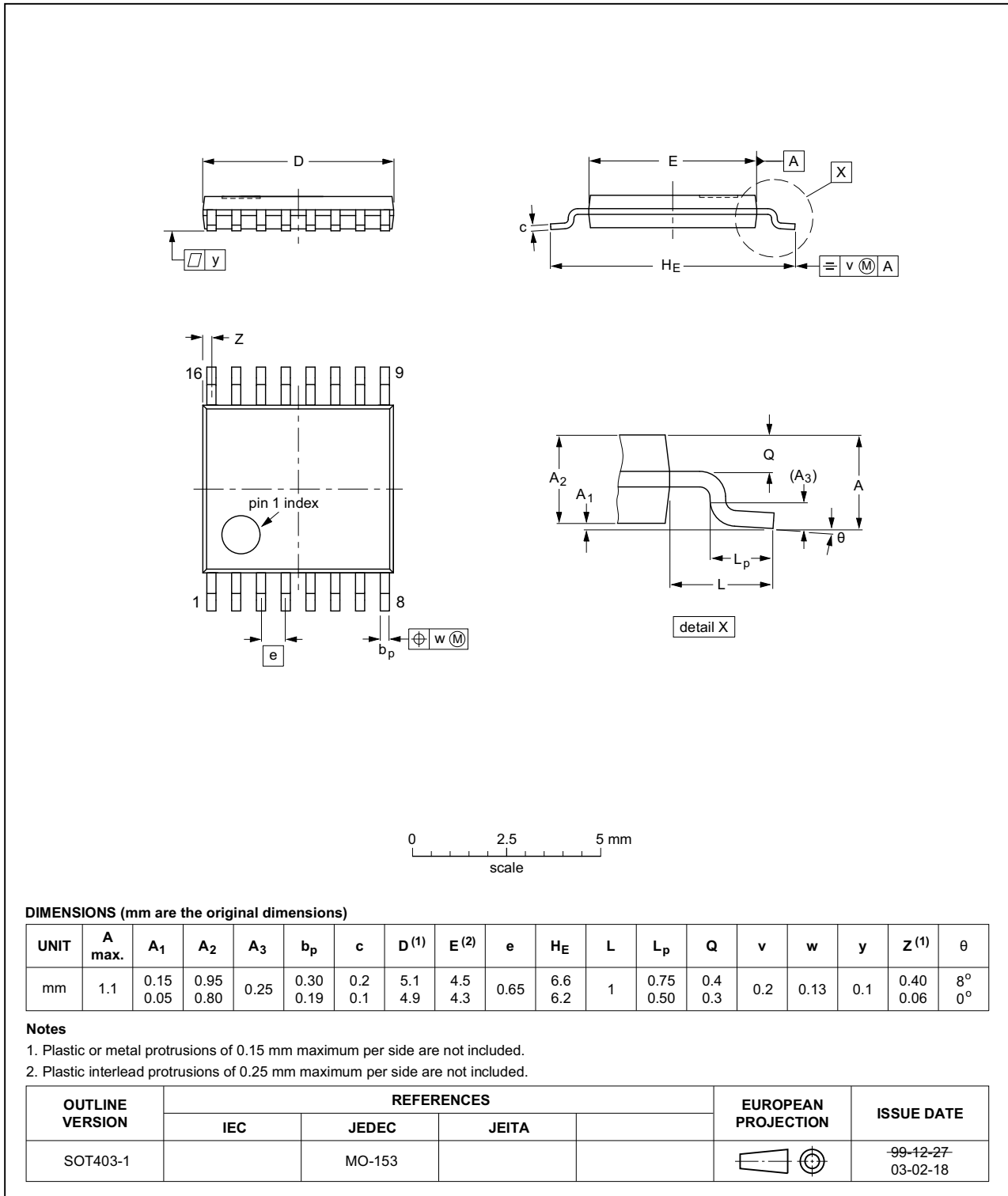


Fig 11. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT139_Q100 v.1	20140619	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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17. Contents

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